

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A process used in fabricating a liquid crystal display, comprising the steps of:

- a) preparing a substrate having a major surface;
- b) patterning a first conductive material layer into plural gate layers and plural storage electrode layers on said major surface;
- c) covering said plural gate layers and said plural storage electrode layers with a gate insulating layer;
- d) patterning an amorphous silicon layer into plural amorphous silicon layers on said gate insulating layer;
- e) selectively etching said gate insulating layer together with pieces of residual amorphous silicon to form plural bent contact slits in said gate insulating layer;
- f) patterning a second conductive material layer into plural drain layers and plural source layers; and
- g) patterning a transparent material layer into pixel electrodes respectively held in contact with said plural source layers;

wherein a first bent contact slit of said plural bent contact slits is formed by etching said gate insulating layer together with pieces of said residual amorphous silicon from a top portion of said gate insulating layer through said gate insulating layer to said major surface of said substrate between a first gate layer of said plural gate layers and a first area where a first drain layer of said plural drain layers adjacent to said first gate layer is patterned, and by etching said gate insulating layer together with pieces of said residual amorphous silicon from said top portion of said gate insulating layer through said gate insulating layer to said major surface of said substrate between said first area where said first drain layer is patterned and a first storage electrode layer of said plural storage electrode layers adjacent to said first area.

2. (Cancelled)

3. (New) The process used in fabricating a liquid crystal display of claim 1, further comprising:
 - h) filling said plural bent contact slits with a dielectric material.
4. (New) The process used in fabricating a liquid crystal display of claim 1, wherein said gate insulating layer comprises an insulating material.
5. (New) The process used in fabricating a liquid crystal display of claim 4, wherein said insulating material comprises at least one of SiN_x and SiO_x .
6. (New) The process used in fabricating a liquid crystal display of claim 1, wherein said second conductive material layer comprises a conductive material; and wherein said conductive material is at least one of chromium, molybdenum-tantalum, and a combination of aluminum and tantalum.